

Features

- . Ultrasmall package facilitates miniaturization in end products.
- . Especially suited for use Electret Condenser Microphone for telephone and audio equipments. (ECM)
- . Excellent voltage characteristics.
- . Excellent transient characteristics.
- . Free of Halogen.

Adoption Maximum Ratings/Ta=25

Event	Code	Set	Unit
Gate to Drain Voltage	V _{GDO}	-20	V
Drain Current	I _D	1	m A
Gate Current	I _G	10	m A
Allowable Power Dissipation	P _D	100	m W
Junction Temperature	T _j	150	
Storage Temperature	T _{stg}	-55 to +150	

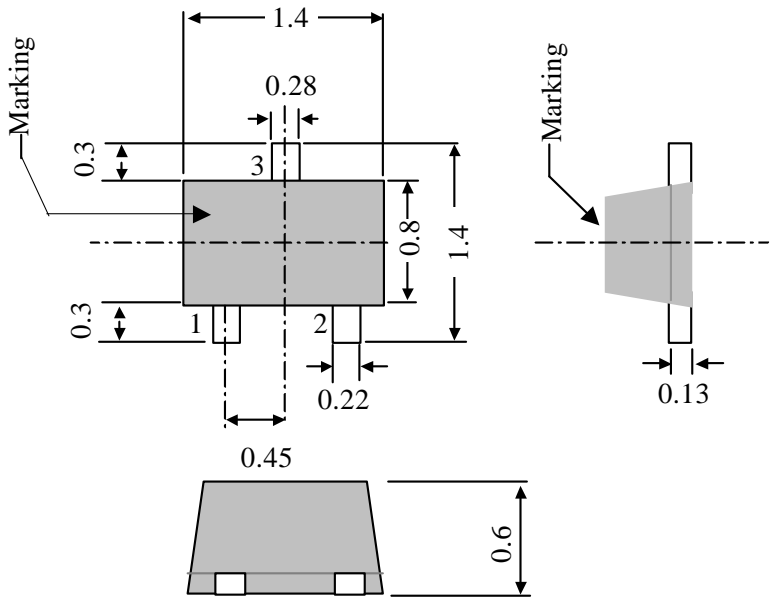
Electrical Characteristics/Ta=25

Event	Code	Set	MIN	TYP	MAX	Unit
G-D Breakdown Voltage	V _{GDO}	I _G = -100uA	-20			V
Drain Current	I _{DSS}	V _{DS} = 2.0 V , V _{GS} = 0	140		350	u A
Gate off Voltage	V _{GS(OFF)}	V _{DS} = 2.0 V , I _D = 1 u A	-0.1		-1.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 2.0 V , V _{GS} = 0 , f = 1KHz	0.5			m S
Input Capacitance	C _{iss}	V _{DS} = 2.0 V , V _{GS} = 0 , f = 1MHz		5.0		p F
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 2.0 V , V _{GS} = 0 , f = 1MHz		1.1		p F

The FJT TF222 is classified by I_{DSS} as follows :(unit:uA)

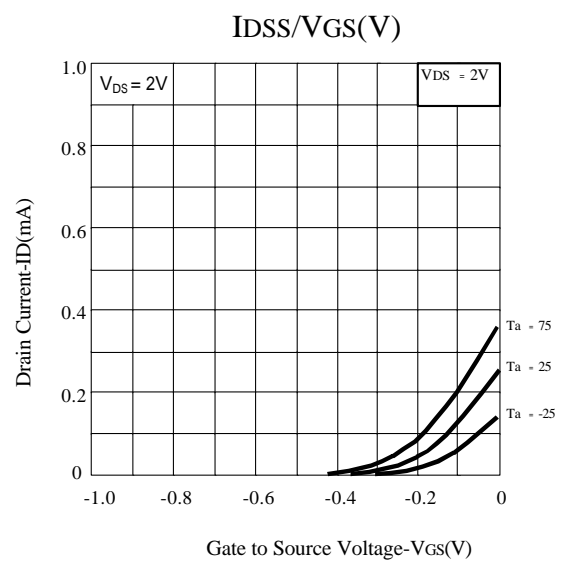
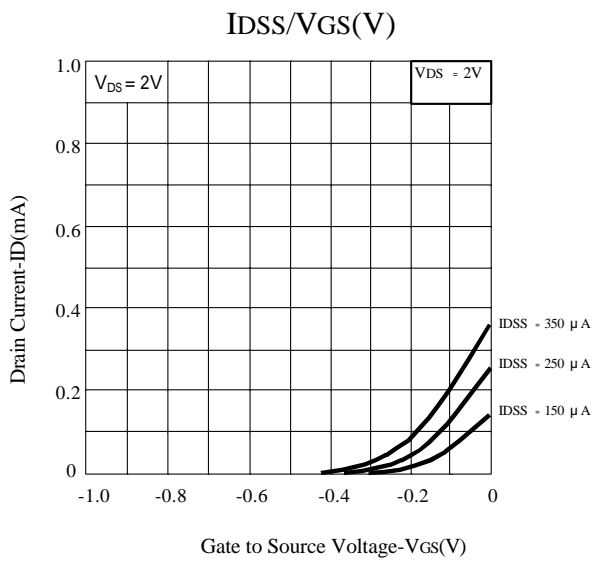
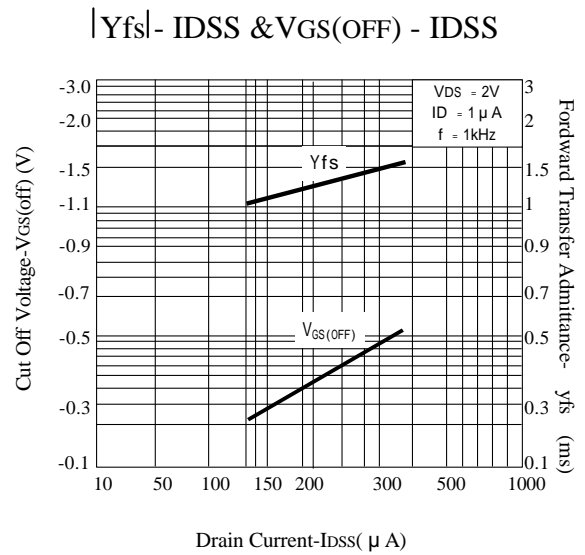
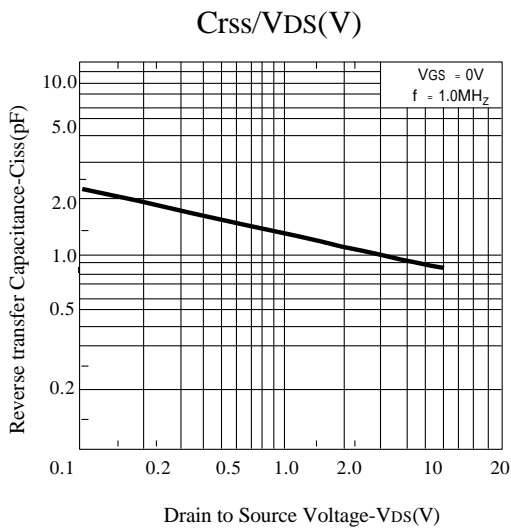
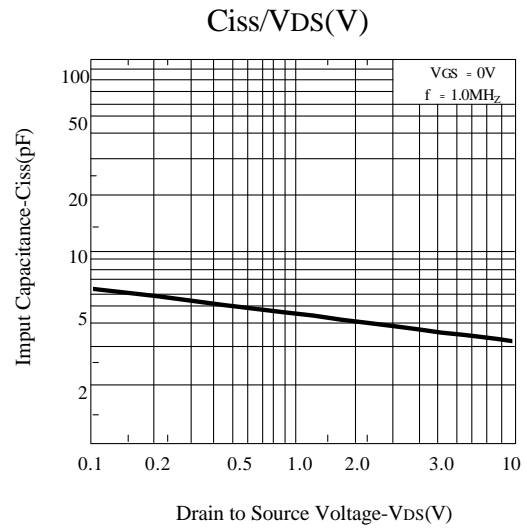
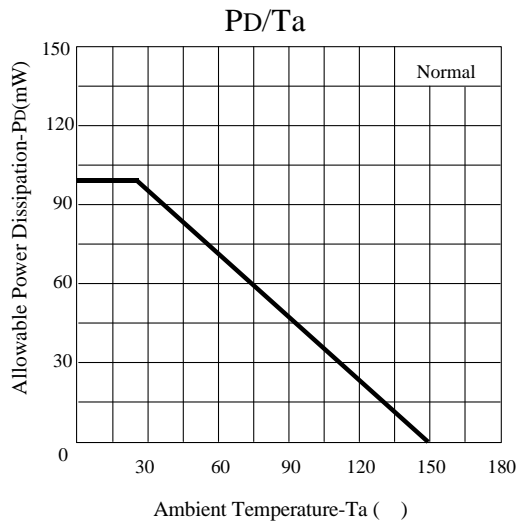
Marking	B4	B5
I _{DSS}	140 to 240	210 to 350

Package Dimensions



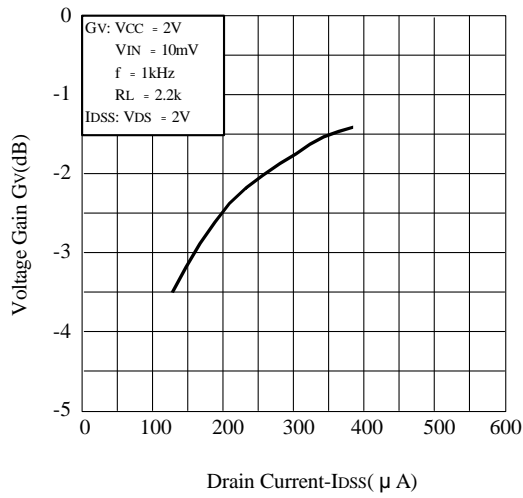
1 : Drain
 2 : Source
 3 : Gate
 SOT-113(unit:mm)

Electrical Characteristics Curve(Ta=25)

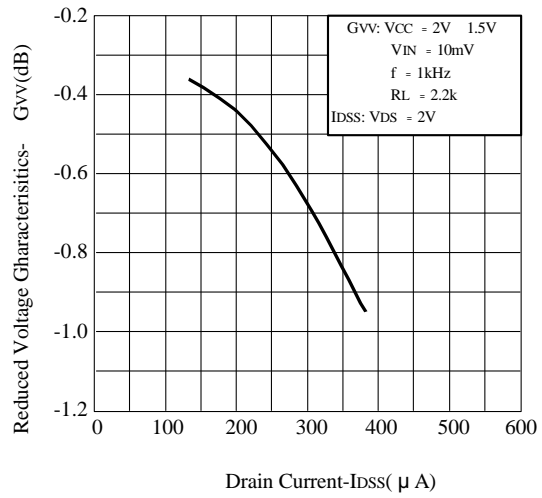


特性曲線(Ta=+25)

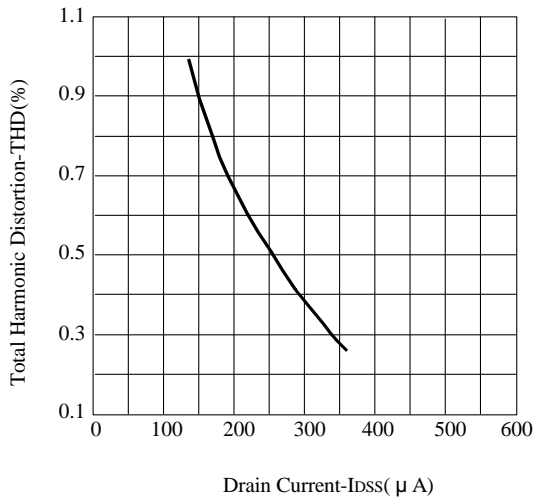
GV/Idss



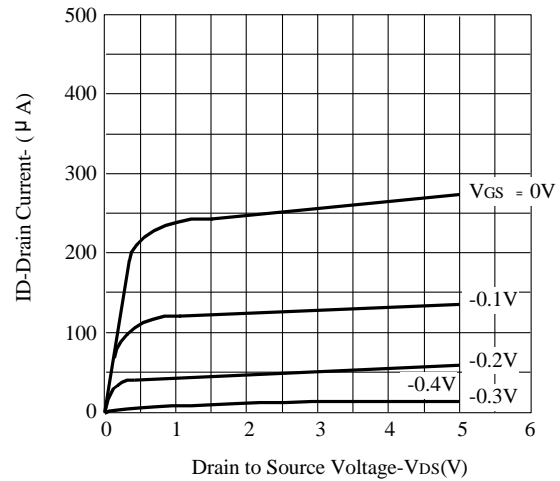
GvV/IdSS



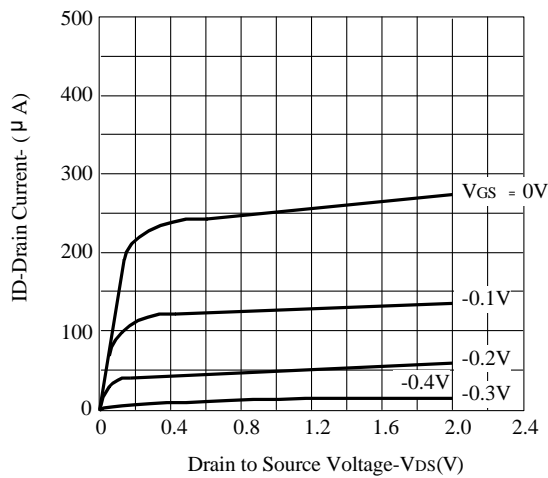
THD/IdSS



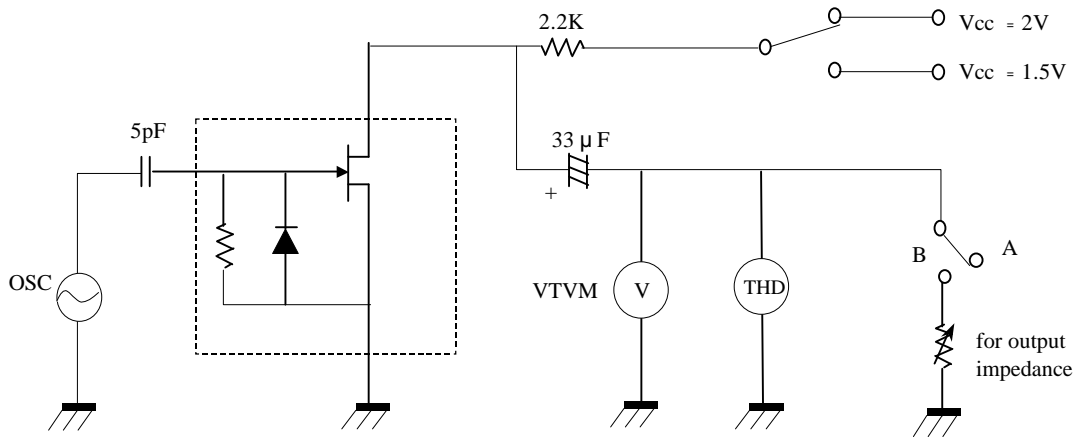
ID-VDS



ID-VDS



TEST CIRCUIT (Ta=25)



PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Voltage Gain	G _v	V _{IN} = 10mV, f = 1KHZ		-2.0		dB
Reduced Voltage Characteristic	G _{VV}	V _{IN} = 10mV, f = 1KHZ , V _{CC} = 2.0V 1.5V		-0.6	-2.0	dB
Frequency Characteristic	G _{vf}	f = 1KHZ to 110HZ			-1.0	dB
Total Harmonic Distortion	THD	V _{IN} = 30mV, f = 1KHZ		0.7		%
Output Noise Voltage	V _{NO}	V _{IN} = 0V, A CURVE			-102	dB